

WEST Search History for Application 10597432

Creation Date: 2008102709:45

Query	DB	Op.	Plur.	Thes.	Date
(\"20010044180\" !\"20030022457\" !\"4877750\" !\"5776628\" !\"6020234\" !\"6057188\" !\"6150210\" !\"6190988\" !\"6204112\" !\"6319788\" !\"6326261\").PN.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-26-2008
(trench same capacitor)	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
((trench same capacitor)) and (DRAM or dynamic random access memory)	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
((trench same capacitor) and (DRAM or dynamic random access memory)) and (plate near4 (connect\$ or contact))	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
((trench same capacitor) and (DRAM or dynamic random access memory) and (plate near4 (connect\$ or contact))) and ((third or three) near3 (dielectric or insulat\$))	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
((trench same capacitor) and (DRAM or dynamic random access memory) and (plate near4 (connect\$ or contact))) and ((third or three) near3 (dielectric or insulat\$) same (storage or plate))	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
((trench same capacitor) and (DRAM or dynamic random access memory) and (plate near4 (connect\$ or contact))) and ((third or three) near3 (dielectric or insulat\$) same (storage or plate)).clm.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
((trench same capacitor) and (DRAM or dynamic random access memory) and (plate near4 (connect\$ or contact)) and ((third or three) near3 (dielectric or insulat\$) same (storage or plate))) and (dopant or implant\$)	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
"thomas" near3 "dyer".inv.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008

("thomas" near3 "dyer".inv.) and ((trench same capacitor) and (DRAM or dynamic random access memory) and (plate near4 (connect\$ or contact)) and ((third or three) near3 (dielectric or insulat\$)))	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
"carl" near2 "radens".inv.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
("carl" near2 "radens".inv.) and ((trench same capacitor) and (DRAM or dynamic random access memory) and (plate near4 (connect\$ or contact)) and ((third or three) near3 (dielectric or insulat\$)))	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008